Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

Features

- Blocking Voltage of 600 thru 800 Volts
- On-State Current Rating of 8 Amperes RMS at 80°C
- High Surge Current Capability 80 Amperes
- Rugged, Economical TO-220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- High Immunity to dv/dt 100 V/µsec Minimum at 125°C
- These are Pb-Free Devices*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR8MG MCR8NG	V _{DRM,} V _{RRM}	600 800	٧
On-State RMS Current (180° Conduction Angles; T _C = 80°C)	I _{T(RMS)}	8.0	Α
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _C = 125°C)	I _{TSM}	80	Α
Circuit Fusing Consideration (t = 8.33 ms)	I ² t	26.5	A ² sec
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C)	P _{GM}	5.0	W
Forward Average Gate Power (t = 8.3 ms, T _C = 80°C)	P _{G(AV)}	0.5	W
Forward Peak Gate Current (Pulse Width \leq 1.0 μ s, T _C = 80°C)	I _{GM}	2.0	Α
Operating Junction Temperature Range	T _J	-40 to 125	°C
Storage Temperature Range	T _{stg}	-40 to 150	°C

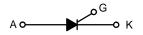
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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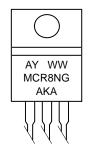
SCRs 8 AMPERES RMS 600 thru 800 VOLTS



MARKING DIAGRAM







A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Diode Polarity

PIN ASSIGNMENT				
1	Cathode			
2	Anode			
3	Gate			
4	Anode			

ORDERING INFORMATION

Device	Package	Shipping
MCR8NG	TO-220AB (Pb-Free)	50 Units / Rail

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T _L	260	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Forward or Reverse Blocking Current $(V_D = Rated V_{DRM} and V_{RRM}; Gate Open)$	T _J = 25°C T _J = 125°C	I _{DRM} , I _{RRM}	_ _	_ _	0.01 2.0	mA
ON CHARACTERISTICS						
Peak Forward On-State Voltage (Note) (I _{TM} = 16 A)		V _{TM}	-	_	1.8	V
Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ V}; R_L = 100 \Omega)$		I _{GT}	2.0	7.0	15	mA
Holding Current (V _D = 12 V, Gate Open, Initiating Current = 200 mA)		I _H	4.0	17	30	mA
Latch Current $(V_D = 12 \text{ V}, I_G = 15 \text{ mA})$		ΙL	6.0	20	40	mA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 \ V; \ 100 \ \Omega)$	T _J = 25°C	V _{GT}	0.5	0.65	1.0	V
Gate Non–Trigger Voltage $(V_D = 12 \text{ V}; R_L = 100 \Omega)$	T _J = 125°C	V_{GD}	0.2	-	-	V
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 125°C)		dv/dt	100	250	_	V/μs
Critical Rate of Rise of On–State Current IPK = 50 A, Pw = 40 μsec, diG/dt = 1 A/μsec, lgt = 50 mA		di/dt	-	-	50	A/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

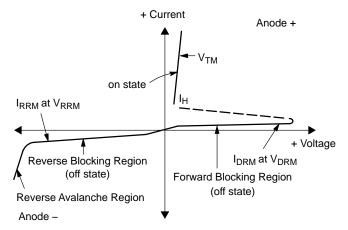
2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

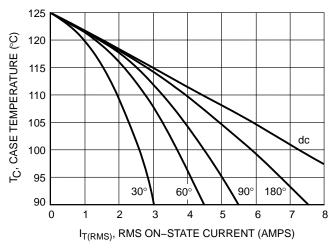
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Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
IH	Holding Current

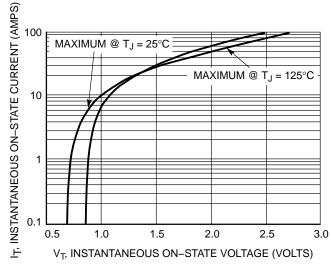




P(AV), AVERAGE POWER DISSIPATION (WATTS) 18 16 180° 90° 14 60° 12 30° 10 8 6 4 2 3 8 $I_{T(AV)}$, AVERAGE ON-STATE CURRENT (AMPS)

Figure 1. Typical RMS Current Derating

Figure 2. On-State Power Dissipation



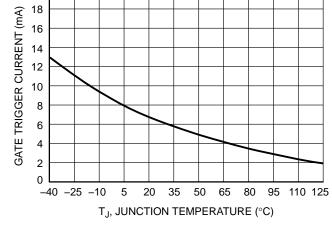


Figure 3. Typical On-State Characteristics

Figure 4. Typical Gate Trigger Current versus **Junction Temperature**

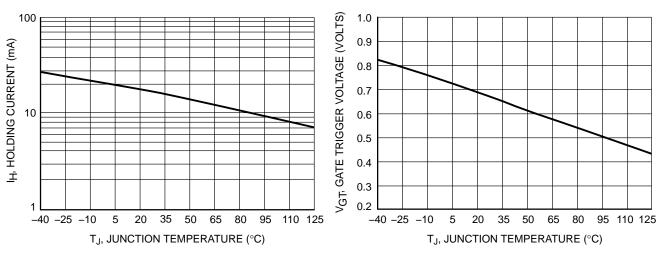


Figure 5. Typical Holding Current versus Junction Temperature

Figure 6. Typical Gate Trigger Voltage versus
Junction Temperature

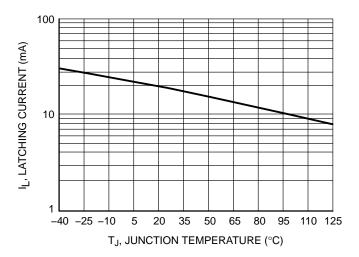
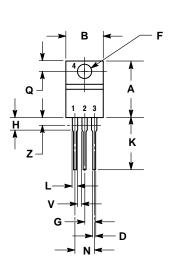
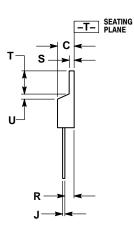


Figure 7. Typical Latching Current versus Junction Temperature

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INC	INCHES		IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 3:

PIN 1. CATHODE

- 2. ANODE
- GATE
- ANODE

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